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	USN		Collage of Engg 8		10ELN 15/25				
	First/Second Semester B.E. Degree Examination, June/July 2014								
Basic Electronics									
	Time: 3 hrs.				Max. Marks:100				
 0 ₽	Note: 1. Answer 2. Answer 3. Answer	any FIVE full q all objective typ to objective type	uestions, choosing at l e questions only in OM questions on sheets ot	east two from each p IR sheet page 5 of the her than OMR will no	art. e answer booklet. ot be valued.				
_			PART — A						
d	1 a. Choose the	correct answer	s for the following :		(04 Marks)				
<u>\$2</u>	i) Ze	ner diode can be	used for rectification. T	This statement is					
Bu	A)	true	6.1	B) false					
	C)	neither true nor	talse	D) none of these					
.g g	ii) The r		$P \leq 0.40$	1100000000000000000000000000000000000	D) 81 204				
P2 ¹¹	A) iii) The	40.0% knee voltage of	D) 00.4%	C) 78.5%	D) 01.270				
rt,		0 3V	B) 0 5V	(C) 0.7V	D) none of these				
	iv) If f H	Iz is the frequent	cy of the input given to	a half wave rectifier	the output frequency				
m: _	wi	ll be	ley of the input Breen to	ot I	, the surplic frequency				
U a	A)	2f Hz	B) f Hz	C) 3f Hz	D) 0.5f Hz				
p, n	,		,	,	,				
1,,	b. Draw and	explain the VI –	- characteristics of a Si-	-diode and Ge-diode.	(06 Marks)				
g ∎ 1 "5	c. With a nea	at circuit diagram	m, explain the working	principles of full way	ve bridge rectifier and				
1 00 1	show that	t the ripple facto	or $= 0.48$, and efficiency	= 81.2%.	(10 Marks)				
Lu 8			, CO						
∲1 g									
$\frac{3}{5}$	2 a. Choose the	correct answer	s for the following :	- f	(04 Marks)				
Έ2. с.fl		e current condu	ction in BJ1 is because	D) heles					
	\mathbf{II}, \mathbf{A}	both electrons	and holes	D) none of these					
	ii) If	a = 0.95 then the	and noics	D) none of these					
- \$; Q	Π) Π Δ`	a = 0.95, men u a = 0.95	$\frac{13}{13}$ of transister	C) 100	D) 120				
$=\frac{42}{4}$ i	ii) Common col	ector arrange	ement is generally	used for	D) 120				
8 71	A)	impedance mat	ching	B) voltage amplific	ation				
>,'``	C	current amplifie	er	D) none of these					
T, <u>c</u>	iv) T	he current relation	onship between two cum	ent gain in a transistor	is				
3- 7	A \	10 a	1 + a	$\frac{1}{12}$ 1-a	D) $12 - \frac{1+13}{2}$				
<u>0</u> ,	A)	$13 \equiv 1$ ot	B) 13 = 1 —a	$C_{13} = 1 + a$	<u></u> D) 15 – <u></u>				
O					·				
4J	b. Draw inpu	it and output ch	aracteristics of an NPN	N transistor in comme	on base configuration				
U Z	and expl	ain.			(10 Marks)				
čš	c. For a Sili	con transistor	a_d , = 0.995, emitter cu	urrent is 10 mA and	leakage current 1,,, is				
Ď	0.511A. I	Find lc, IB , B and	Icro.		(06 Marks)				
-7.									

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3 a. Cho	ose the correct ans	w(te		(04 Marks)
	i) Which of the fo	llowing factor affects the	Q-point stability?	· · · · · ·
	A) I _{co}	C	B) coupling capaci	tor
	C) emitter resis	tor	D) bypass capacito	r
	ii) The inter section	n of the dc load line with s	given base current curv	e is the
	A) h-point	B) D-point	C) O-point	D) none of these
	iii) For an emitter for	ollower, the voltage gain is	S	,
	A) unity	B) greater than un	ity C) less than unity	D) zero
	iv) The best biasing	g stability is achieved by u	using biasing m	ethod.
	A) fixed	B) collector to base	C) voltage divider	D) none of these
b. H e c. I	Explain the working or equation for IB. Define stability factor	of collector-to-base bias c	rcuit using an NPN tra at cause instability of h	nsistor and derive the (08 Marks)
•• -				(08 Marks)
4 a. Ch	oose the correct ans	wers for the following		(04 Marks)
]	i) FET is a	_ controlled device.		D
	A) voltage	B) current	C) pulse	D) power
]	1) PNPN device is	an		
	A) UJT	B) SCR	C) MOSFET	D) MODFET
1	iii) used as	s a relaxation oscillator.		
	A) MOSFET	B) SCR	C) BJT	ek) UJT
1	iv) The intrinsic sta	ndoff ratio of UJT		•.
	A) equal to one		B) must be less tha	n unity
	C) must be grea	ter than unity	D) must be zero	
b. I	Explain the working	of two transistor model	of an SCR and obtain	the expression for the
8	node current.	(08 Marks)		
c. I	Draw the equivalent c	ircuit and VI-characteristi	c of UJT and explain it	. (08 Marks)
1				
		PART — E		
5 a.	Choose the correct an	swers for the following :		(04 Marks)
i) Oscillator uses	type of feedback.		
	A) positive	B) negative	C) reverse	D) both A and B
i	i) The frequency of	of oscillations in an oscilla	tor is given by	-
		P) 2TEL C	C) 2 in I C	
	A) 2rcLC	B) 21EEC	C) 21C LC	$\frac{D}{2n-4:C}$
ł	ni) With negative fee	dback the bandwidth of	an amplifier	
1	A) decreases	B) increases	C) both A and B	D) constant
i	y) The magnitude vo	oltage gain at half power	frequencies of an RC	Coupled amplifier is
1	times max	imum voltage gain	inequencies of united	
	$\underline{\qquad} A) 0 707$	B) 7 07	C) 10	D) 17.06
		2,	-,	_,
b.]	Draw the frequency	response of an RC-cou	pled amplifier and ex	xplain it. Mention its
é	advantages and disadv	vantages.		(08 Marks)
c.]	Explain with the help	o of circuit diagram the w	orking of an RC phas	e shift oscillator using
t	ransistor.			(06 Marks)

d. In a transistor colpitts oscillator having tank circuit parameters as ci = 0.001 ILE and c? = 0.01 pF if L = 51AH, calculate the frequency of oscillations. (02 Marks)

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		And And				
6 a. Cho	ose the correct answ	ver;		(04 Marks)		
i) The gain of the v	oltage follower is	()	\mathbf{D}) and \mathbf{H}		
	A) zero	B) infinite	C) negative	D) unity		
]	$\frac{1}{1}$	gain of op-amp is	C) 00	D) positive		
i	iii) The CMRR is gi	ven by	C) 00	D) positive		
	$\begin{array}{c} \text{A)} \text{Ad } \mathbf{x} \text{ A} \\ \end{array}$	$\frac{B}{A} / Ad$	C) Ad $/A_{a}$	D) none of these		
i	iv) Maximum rate of	f change of output volta	ge with time is called			
	A) CMRR	B) slew rate	C) over rate	D) none of these		
b I	ist the characteristics	of an ideal-op-amp and	draw the three input i	nverting summer circuit		
υ	ising an op-amp and d	erive an expression for o	output voltage.	(08 Marks)		
c. I	Draw the basic block d	iagram of a cathode ray	tube and explain its w	orking. (08 Marks)		
7 a. Cho	ose the correct answ	ers for the following :		(04 Marks)		
	i) Two's compliant	of $(1001)_2$ is		(**************************************		
	A) 1001	B) 0010	C) 0111	D) 1010		
i	ii) To represent 35 i	n binary, number of bits	s required is			
	A) 6	B) 5	C) 4	D) 33		
1	iii) Decimal number	37 is represented in BC	C) 00110111			
	A) 100111 iv) Over modulation	B) 00111011 exists when modulation	C 00110111			
	A) 1	B) 0	C) > 1	D) < 1		
		2) 0				
b. I	Explain the need for m	odulation.		(06 Marks)		
c. (Convert (A3B)16 = ()10, and $(247.75)10 = (22.15$		(04 Marks)		
d. 1	1) Perform (FCO2A) 10^{11}	$D = (D052)_{\perp}$, using 16's $P = (A2, 245)_{\parallel}$ using 16's	complement.	(06 Morta)		
	II) Subtract (4517.04)	5 ITOIII (42.545)8 using a	s s complement.	(UO WIARKS)		
8 a. Cho	ose the correct answ	ers for the following :		(04 Marks)		
	i) The expression f	or half adder carry with	input A and B is given	ı by		
	A) $A + B$	B) AB	C) A B	D) none of these		
	ii) The complement	t of A + B + 1 is	_			
	A) 0	B) A + 1	C) AB + 1	D) 1		
-	iii) ABCD + ABD is	s equal to				
	A) ABC	B) ABC	C) ABD	D) ABD		
	A + (B + C) (A	(A + B) + C is	law.	D) none of these		
	A) associative	D) commutative	C) distributive	D) none of these		
b. I	Design a full adder circ	cuit and realize, using ty	vo half adders.	(08 Marks)		
c. §	c. Simplify the following expressions and implement using only NAND gates :					
i) $Y = ABC + ABC $	ABC + ABC				
i	i) $Y = AB + AC$					
1 1	i) $Y = A + AR$			(Al Marka)		
1	$\mathbf{n}_{j} \mathbf{i} = \mathbf{n} + \mathbf{n} \mathbf{D} .$			(00 WIATKS)		

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